HF / VHF power LDMOS transistor

AMPLEON

Rev. 4 — 1 December 2016

Product data sheet

1. Product profile

1.1 General description

A 500 W to 600 W LDMOS power transistor for broadcast applications and industrial applications in the HF to 500 MHz band.

Table 1. Application information

Mode of operation	f	V _{DS}	P_L	Gp	η_D
	(MHz)	(V)	(W)	(dB)	(%)
CW	225	50	500	26.5	70
	108	50	600	27.5	73

1.2 Features and benefits

- Typical CW performance at frequency of 225 MHz, a supply voltage of 50 V and an I_{Dq} of 1000 mA:
 - ◆ Average output power = 500 W
 - ◆ Power gain = 26.5 dB
 - ◆ Efficiency = 70 %
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (10 MHz to 500 MHz)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- Industrial, scientific and medical applications
- Broadcast transmitter applications

HF / VHF power LDMOS transistor

2. Pinning information

Table 2. Pinning

Description	Simplified outline	Graphic symbol
drain1		
drain2	1 2	1
gate1	5	3
gate2	3 4	5
source	[1]	4
		<u>'</u>
		2 sym117
	drain1 drain2 gate1 gate2	drain1 drain2 gate1 gate2

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Name Description Version	
BLF574		flanged balanced LDMOST ceramic package; 2 mounting holes; 4 leads	SOT539A

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	110	V
V_{GS}	gate-source voltage		-0.5	+11	V
I _D	drain current		-	56	Α
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	225	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	T _{case} = 80 °C; P _L = 400 W	0.23	K/W

[1] $R_{th(j-c)}$ is measured under RF conditions.

HF / VHF power LDMOS transistor

6. Characteristics

Table 6. DC characteristics

 T_i = 25 °C; per section unless otherwise specified.

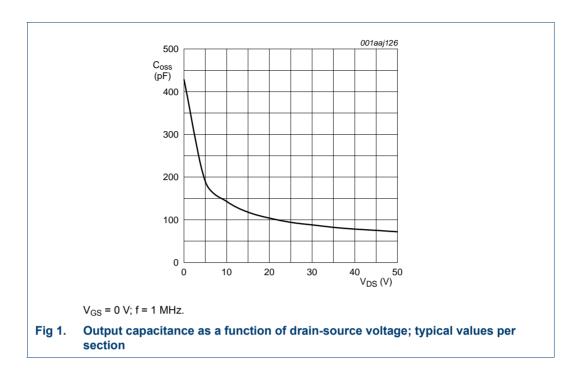
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.5 \text{ mA}$	110	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 250 mA	1.25	1.7	2.25	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 50 V; I _D = 500 mA	1.35	1.85	2.35	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 50 V	-	-	2.8	μА
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	29	37.5	-	A
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	280	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 12.5 A	-	17	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 8.33 \text{ A}$	-	0.14	-	Ω
C _{rs}	feedback capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$ f = 1 MHz	-	1.5	-	pF
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V};$ f = 1 MHz	-	204	-	pF
C _{oss}	output capacitance	V _{GS} = 0 V; V _{DS} = 50 V; f = 1 MHz	-	72	-	pF

Table 7. RF characteristics

Mode of operation: CW; f = 225 MHz; RF performance at V_{DS} = 50 V; I_{Dq} = 1000 mA for total device; T_{case} = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _L = 400 W	25	26.5	28	dB
RLin	input return loss	P _L = 400 W	13	20	-	dB
η_{D}	drain efficiency	P _L = 400 W	66	70	-	%

HF / VHF power LDMOS transistor



6.1 Ruggedness in class-AB operation

The BLF574 is capable of withstanding a load mismatch corresponding to VSWR = 13 : 1 through all phases under the following conditions: V_{DS} = 50 V; I_{Dq} = 1000 mA; P_L = 400 W; f = 225 MHz.

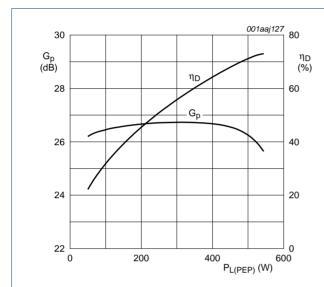
4 of 19

7. Application information

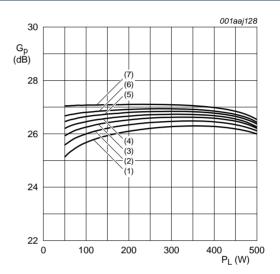
7.1 RF performance

RF performance in a 500 W application circuit at 225 MHz.

7.1.1 1-Tone CW



 V_{DS} = 50 V; I_{Dq} = 1000 mA; f = 225 MHz.



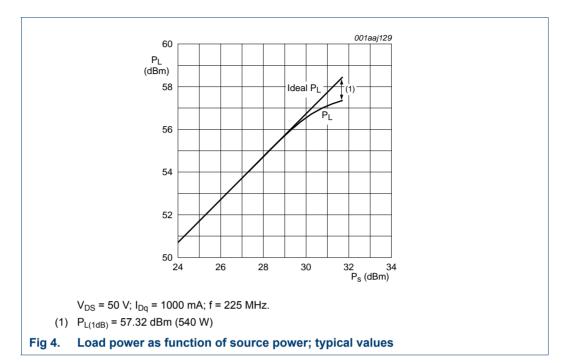
 V_{DS} = 50 V; f = 225 MHz.

- (1) $I_{Dq} = 400 \text{ mA}$
- (2) $I_{Dq} = 600 \text{ mA}$
- (3) $I_{Dq} = 800 \text{ mA}$
- (4) $I_{Dq} = 1000 \text{ mA}$
- (5) $I_{Dq} = 1200 \text{ mA}$
- (6) $I_{Dq} = 1400 \text{ mA}$
- (7) $I_{Dq} = 1800 \text{ mA}$

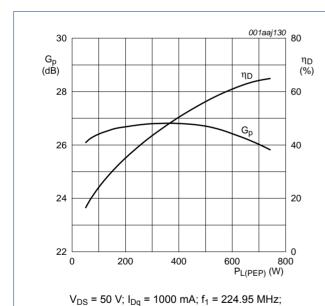
Fig 2. Power gain and drain efficiency as functions of load power; typical values

Fig 3. Power gain as function of load power; typical values

HF / VHF power LDMOS transistor

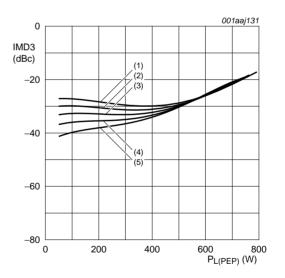


7.1.2 2-Tone CW



 $f_2 = 225.05 \text{ MHz}.$

Fig 5. Power gain and drain efficiency as functions of peak envelope load power; typical values



 V_{DS} = 50 V; f_1 = 224.95 MHz; f_2 = 225.05 MHz.

- (1) $I_{Dq} = 600 \text{ mA}$
- (2) $I_{Dq} = 800 \text{ mA}$
- (3) $I_{Dq} = 1000 \text{ mA}$
- (4) $I_{Dq} = 1200 \text{ mA}$
- (5) $I_{Dq} = 1400 \text{ mA}$

Fig 6. Third order intermodulation distortion as a function of peak envelope load power; typical values

HF / VHF power LDMOS transistor

7.1.3 Application circuit

Table 8. List of components

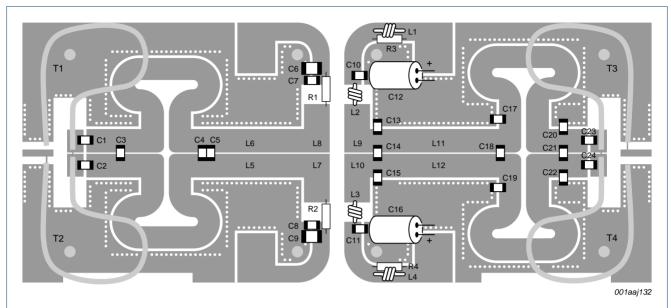
For application circuit, see Figure 7.

Printed-Circuit Board (PCB): Rogers 5880; ε_r = 2.2 F/m; height = 0.79 mm; Cu (top/bottom metallization); thickness copper plating = 35 μ m.

Component	Description	Value	Remarks
C1, C2, C23, C24	multilayer ceramic chip capacitor	100 pF [1]	
C3	multilayer ceramic chip capacitor	24 pF [1]	
C4, C5	multilayer ceramic chip capacitor	39 pF [1]	
C6, C9	multilayer ceramic chip capacitor	4.7 μF	TDK4532X7R1E475Mt020U
C7, C8, C10, C11	multilayer ceramic chip capacitor	1 nF 🗓	
C12, C16	electrolytic capacitor	220 μF; 63 V	
C13, C15	multilayer ceramic chip capacitor	62 pF [1]	
C14	multilayer ceramic chip capacitor	15 pF [1]	
C17, C19	multilayer ceramic chip capacitor	47 pF [1]	
C18	multilayer ceramic chip capacitor	33 pF [1]	
C20, C22	multilayer ceramic chip capacitor	10 pF [1]	
C21	multilayer ceramic chip capacitor	18 pF [1]	
L1, L2, L3, L4	3 turns 1 mm copper wire	D = 3 mm; length = 3 mm	
L5, L6	stripline	-	(L × W) 125 mm × 7 mm
L7, L8, L9, L10	stripline	-	(L × W) 8 mm × 15 mm
L11, L12	stripline	-	(L × W) 132 mm × 7 mm
R1, R2	metal film resistor	10 Ω; 0.6 W	
R3, R4	metal film resistor	3 Ω; 0.6 W	
T1, T2, T3, T4	semi rigid coax	50 Ω; 120 mm	EZ-141-AL-TP-M17

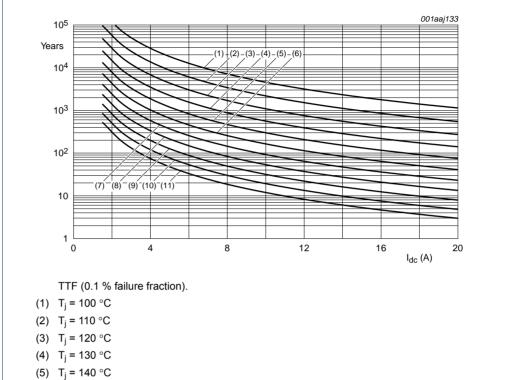
^[1] American Technical Ceramics type 100B or capacitor of same quality.

HF / VHF power LDMOS transistor



HF / VHF power LDMOS transistor

7.2 Reliability



- (6) $T_i = 150 \, ^{\circ}\text{C}$
- (7) $T_i = 160 \, ^{\circ}\text{C}$ (8) $T_i = 170 \, ^{\circ}\text{C}$
- (9) $T_i = 180 \, ^{\circ}C$
- (10) $T_i = 190 \, ^{\circ}C$
- (11) $T_i = 200 \, ^{\circ}C$

BLF574 electromigration (I_D, total device) Fig 8.

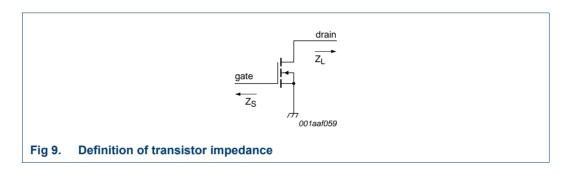
HF / VHF power LDMOS transistor

8. Test information

8.1 Impedance information

Table 9.Typical impedanceSimulated Z_S and Z_L test circuit impedances.

f	Zs	Z _L
MHz	Ω	Ω
225	3.2 + j2.5	7.5 + j4.0

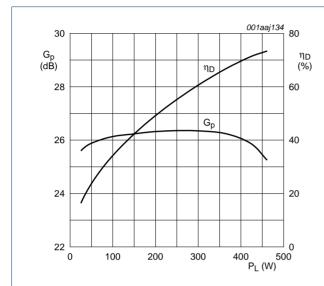


HF / VHF power LDMOS transistor

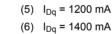
8.2 RF performance

The following figures are measured in a class-AB production test circuit.

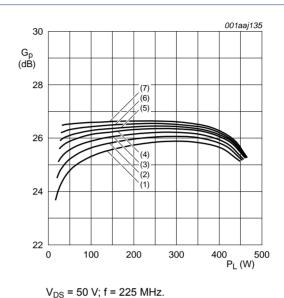
1-Tone CW 8.2.1



 $V_{DS} = 50 \text{ V}$; $I_{Dq} = 1000 \text{ mA}$; f = 225 MHz.



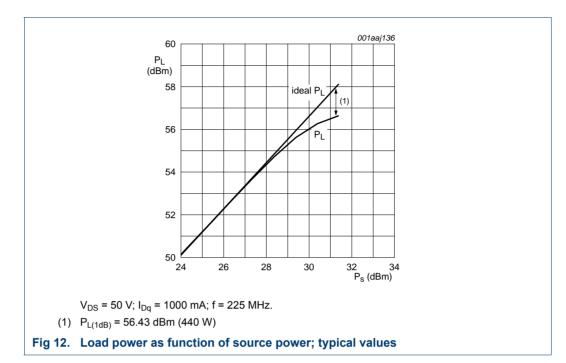




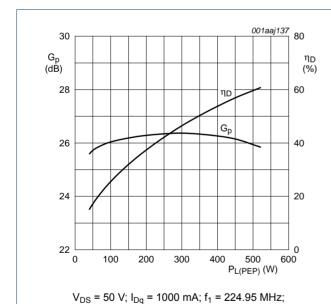
- (1) $I_{Dq} = 400 \text{ mA}$
- (2) $I_{Dq} = 600 \text{ mA}$
- (3) $I_{Dq} = 800 \text{ mA}$ (4) $I_{Dq} = 1000 \text{ mA}$
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Fig 11. Power gain as function of load power; typical values

HF / VHF power LDMOS transistor

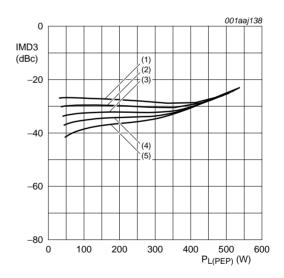


8.2.2 2-Tone CW



f₂ = 225.05 MHz.

Fig 13. Power gain and drain efficiency as functions of peak envelope load power; typical values



 V_{DS} = 50 V; f_1 = 224.95 MHz; f_2 = 225.05 MHz.

- (1) $I_{Dq} = 600 \text{ mA}$
- (2) $I_{Dq} = 800 \text{ mA}$
- (3) $I_{Dq} = 1000 \text{ mA}$
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- (5) $I_{Dq} = 1400 \text{ mA}$

Fig 14. Third order intermodulation distortion as a function of peak envelope load power; typical values

HF / VHF power LDMOS transistor

8.2.3 Test circuit

Table 10. List of components

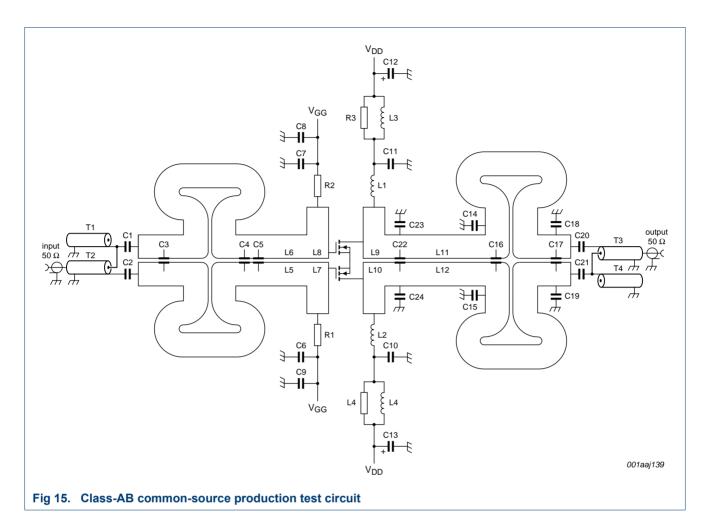
For production test circuit, see Figure 15 and Figure 16.

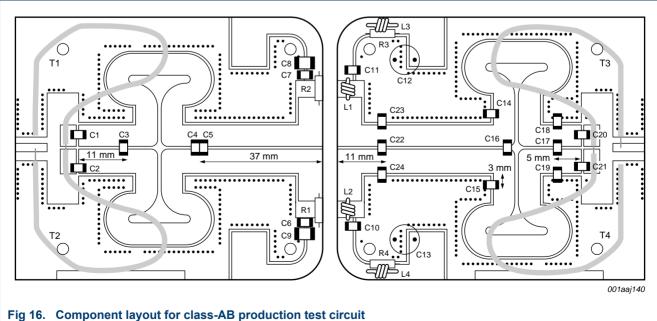
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C14, C15	multilayer ceramic chip capacitor	47 pF [1]	
C16	multilayer ceramic chip capacitor	33 pF [1]	
C17	multilayer ceramic chip capacitor	18 pF [1]	
C18, C19	multilayer ceramic chip capacitor	10 pF [1]	
C22	multilayer ceramic chip capacitor	15 pF [1]	
C23, C24	multilayer ceramic chip capacitor	62 pF [1]	
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L7, L8, L9, L10	stripline	-	(L × W) 8 mm × 15 mm
L11, L12	stripline	-	(L × W) 132 mm × 7 mm
R1, R2	metal film resistor	10 Ω; 0.6 W	
R3, R4	metal film resistor	3 Ω; 0.6 W	
T1, T2, T3, T4	semi rigid coax	50 Ω; 120 mm	EZ-141-AL-TP-M17

^[1] American Technical Ceramics type 100B or capacitor of same quality.

HF / VHF power LDMOS transistor





HF / VHF power LDMOS transistor

9. Package outline

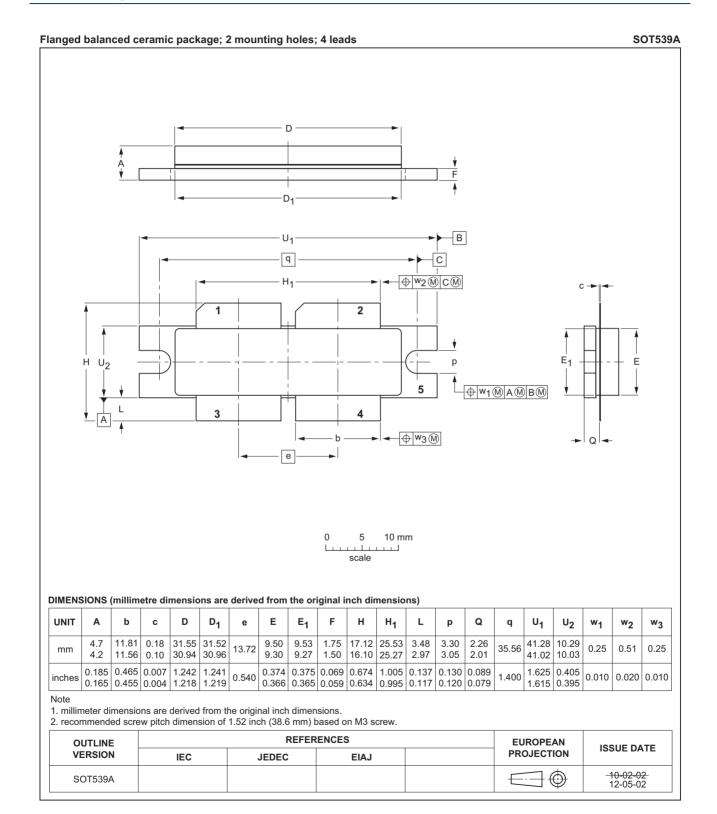


Fig 17. Package outline SOT539A

HF / VHF power LDMOS transistor

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [1]

^[1] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

11. Abbreviations

Table 12. Abbreviations

Acronym	Description	
CW	Continuous Wave	
EDGE	Enhanced Data rates for GSM Evolution	
GSM	Global System for Mobile communications	
HF	High Frequency	
LDMOS	Laterally Diffused Metal-Oxide Semiconductor	
LDMOST	Laterally Diffused Metal-Oxide Semiconductor Transistor	
RF	Radio Frequency	
TTF	Time To Failure	
VHF	Very High Frequency	
VSWR	Voltage Standing-Wave Ratio	

12. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF574 v.4	20161201	Product data sheet	-	BLF574_3
Modifications:	Section 10 on page 16: updated Handling information			
BLF574_3	20150901	Product data sheet	-	BLF574_2
BLF574_2	20090224	Product data sheet	-	BLF574_1
BLF574_1	20081208	Preliminary data sheet	-	-

HF / VHF power LDMOS transistor

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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HF / VHF power LDMOS transistor

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HF / VHF power LDMOS transistor

15. Contents

1	Product profile
1.1	General description 1
1.2	Features and benefits
1.3	Applications
2	Pinning information 2
3	Ordering information
4	Limiting values
5	Thermal characteristics
6	Characteristics
6.1	Ruggedness in class-AB operation 4
7	Application information 5
7.1	RF performance
7.1.1	1-Tone CW
7.1.2	2-Tone CW 6
7.1.3	Application circuit
7.2	Reliability
8	Test information
8.1	Impedance information 10
8.2	RF performance
8.2.1	1-Tone CW
8.2.2	2-Tone CW
8.2.3	Test circuit
9	Package outline
10	Handling information 16
11	Abbreviations
12	Revision history
13	Legal information
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks 18
14	Contact information 18
15	Contents

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